

MA786WK

Silicon epitaxial planer type

For super high-speed switching circuit

For small current rectification

■ Features

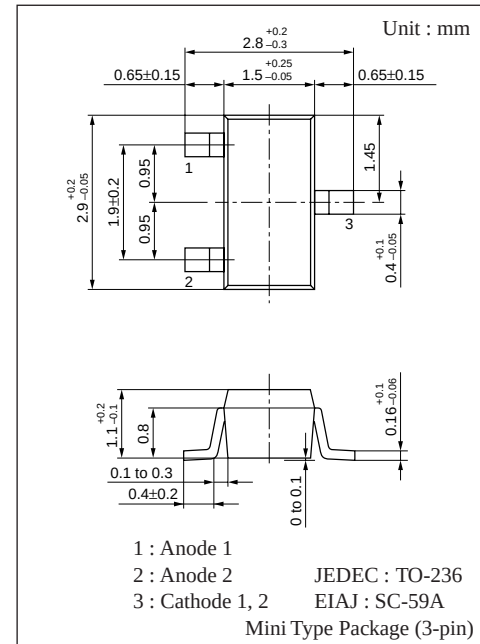
- Two elements are incorporated in MA786 (cathode common)
- $I_{F(AV)}=100\text{mA}$ rectification possible
- Fast reverse recovery time t_{rr} , optimum for high-frequency rectification
- Low V_F (forward voltage) with high rectification efficiency

■ Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	30	V
Repetitive peak reverse voltage	V_{RRM}	30	V
Peak forward current	Single	300	mA
	Double		
Average forward current	Single	100	mA
	Double		
Non-repetitive peak forward surge current	I_{FSM}^{*1}	1	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	- 55 to +125	$^\circ\text{C}$

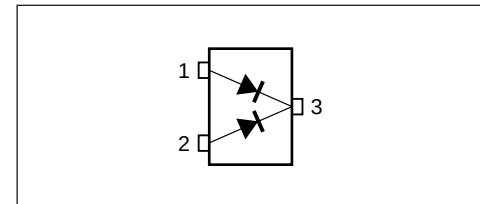
* 1 50Hz sine wave, one-cycle wave, high value (non-repetitive)

* 2 Use value per chip



Marking Symbol : M3Z

■ Internal Connection

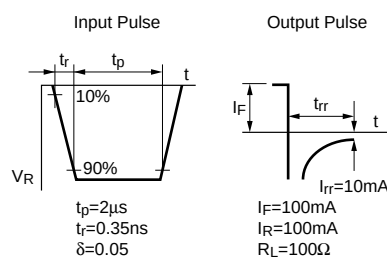
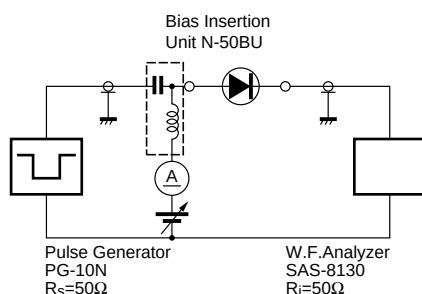


■ Electrical Characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R=30\text{V}$			15	μA
Forward voltage (DC)	V_F	$I_F=100\text{mA}$			0.55	V
Terminal capacitance	C_t	$V_R=0\text{V}, f=1\text{MHz}$		20		pF
Reverse recovery time	t_{rr}^{*}	$I_F=I_R=100\text{mA}$ $I_R=10\text{mA}, R_L=100\Omega$		2		ns

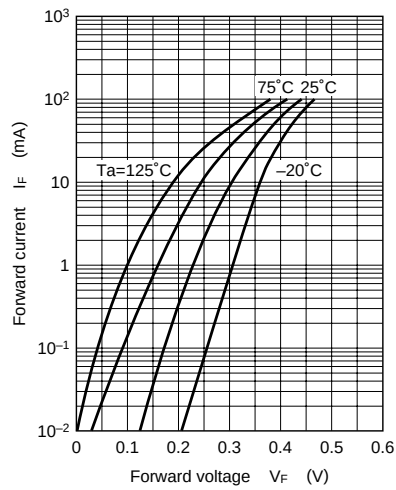
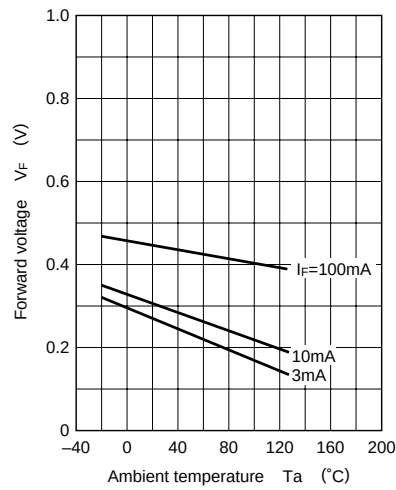
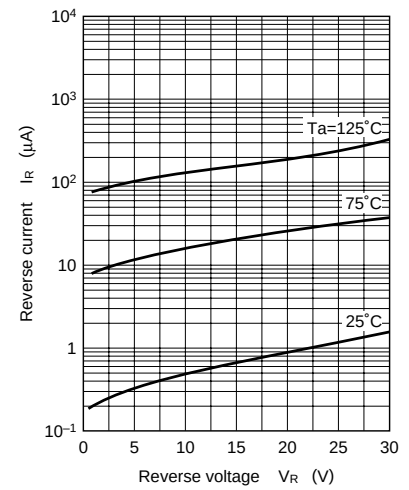
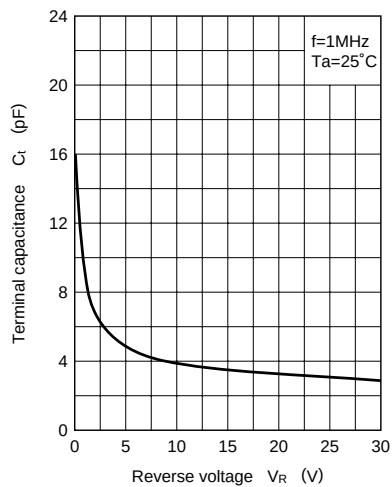
Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.

2. Rated input/output frequency : 250MHz

3. * t_{rr} measuring circuit

■ Marking



$I_F - V_F$  $V_F - T_a$  $I_R - V_R$  $C_t - V_R$  $I_R - T_a$ 